

NTD2955, NVD2955

MOSFET – Power, P-Channel, DPAK

-60 V, -12 A

This Power MOSFET is designed to withstand high energy in the avalanche and commutation modes. Designed for low-voltage, high-speed switching applications in power supplies, converters, and power motor controls. These devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer an additional safety margin against unexpected voltage transients.

Features

- Avalanche Energy Specified
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperature
- Designed for Low-Voltage, High-Speed Switching Applications and to Withstand High Energy in the Avalanche and Commutation Modes
- NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	-60	Vdc
Gate-to-Source Voltage	V_{GS}	± 20	Vdc
– Continuous	V_{GSM}	± 25	Vpk
– Non-repetitive ($t_p \leq 10$ ms)			
Drain Current	I_D	-12	Adc
– Continuous @ $T_a = 25^\circ\text{C}$	I_{DM}	-18	Apk
– Single Pulse ($t_p \leq 10$ ms)			
Total Power Dissipation @ $T_a = 25^\circ\text{C}$	P_D	55	W
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 25$ Vdc, $V_{GS} = 10$ Vdc, Peak $I_L = 12$ Apk, $L = 3.0$ mH, $R_G = 25$ Ω)	E_{AS}	216	mJ
Thermal Resistance	$R_{\theta JC}$	2.73	$^\circ\text{C/W}$
– Junction-to-Case	$R_{\theta JA}$	71.4	
– Junction-to-Ambient (Note 1)	$R_{\theta JA}$	100	
– Junction-to-Ambient (Note 2)			
Maximum Lead Temperature for Soldering Purposes, 1/8 in. from case for 10 seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

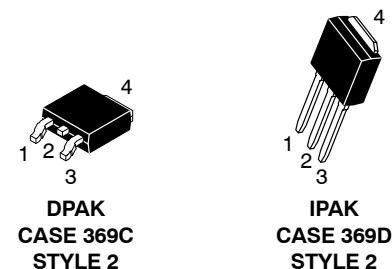
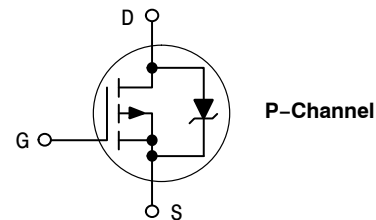
1. When surface mounted to an FR4 board using 1 in pad size (Cu area = 1.127 in²).
2. When surface mounted to an FR4 board using the minimum recommended pad size (Cu area = 0.412 in²).



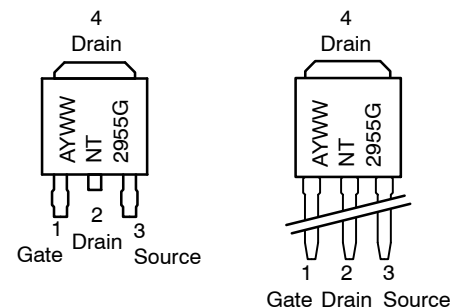
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$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
-60 V	155 m Ω @ -10 V, 6 A	-12 A



MARKING DIAGRAMS & PIN ASSIGNMENTS



A = Assembly Location*
NT2955/NV2955 = Specific Device Code (DPAK)
NT2955 = Specific Device Code (IPAK)
Y = Year
WW = Work Week
G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NTD2955, NVD2955

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (Note 3) (V _{GS} = 0 Vdc, I _D = -0.25 mA) (Positive Temperature Coefficient)	V _{(BR)DSS}	-60 -	- 67	- -	Vdc mV/°C
Zero Gate Voltage Drain Current (V _{GS} = 0 Vdc, V _{DS} = -60 Vdc, T _J = 25°C) (V _{GS} = 0 Vdc, V _{DS} = -60 Vdc, T _J = 150°C)	I _{DSS}	- -	- -	-10 -100	μAdc
Gate-Body Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	-100	nAdc

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = -250 μAdc) (Negative Temperature Coefficient)	V _{GS(th)}	-2.0 -	-2.8 4.5	-4.0 -	Vdc mV/°C
Static Drain-Source On-State Resistance (V _{GS} = -10 Vdc, I _D = -6.0 Adc)	R _{DS(on)}	-	0.155	0.180	Ω
Drain-to-Source On-Voltage (V _{GS} = -10 Vdc, I _D = -12 Adc) (V _{GS} = -10 Vdc, I _D = -6.0 Adc, T _J = 150°C)	V _{DS(on)}		-1.86 -	-2.6 -2.0	Vdc
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 6.0 Adc)	g _{FS}		8.0	-	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = -25 Vdc, V _{GS} = 0 Vdc, F = 1.0 MHz)	C _{iss}	-	500	750	pF
Output Capacitance		C _{oss}	-	150	250	
Reverse Transfer Capacitance		C _{rss}	-	50	100	

SWITCHING CHARACTERISTICS (Notes 3 and 4)

Turn-On Delay Time	(V _{DD} = -30 Vdc, I _D = -12 A, V _{GS} = -10 V, R _G = 9.1 Ω)	t _{d(on)}	-	10	20	ns
Rise Time		t _r	-	45	85	
Turn-Off Delay Time		t _{d(off)}	-	26	40	
Fall Time		t _f	-	48	90	
Gate Charge	(V _{DS} = -48 Vdc, V _{GS} = -10 Vdc, I _D = -12 A)	Q _T	-	15	30	nC
		Q _{GS}	-	4.0	-	
		Q _{GD}	-	7.0	-	

DRAIN-SOURCE DIODE CHARACTERISTICS (Note 3)

Diode Forward On-Voltage (I _S = 12 Adc, V _{GS} = 0 V) (I _S = 12 Adc, V _{GS} = 0 V, T _J = 150°C)	V _{SD}	- -	-1.6 -1.3	-2.5 -	Vdc
Reverse Recovery Time (I _S = 12 A, dI _S /dt = 100 A/μs, V _{GS} = 0 V)	t _{rr}	-	50		ns
	t _a	-	40	-	
	t _b	-	10	-	
Reverse Recovery Stored Charge	Q _{RR}	-	0.10	-	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Indicates Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperature.

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

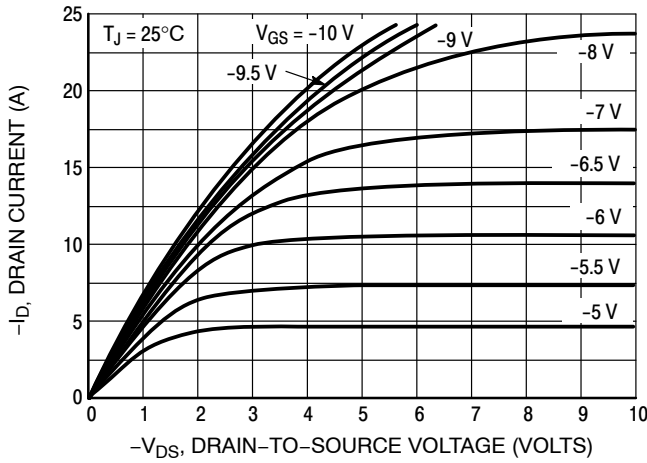


Figure 1. On-Region Characteristics

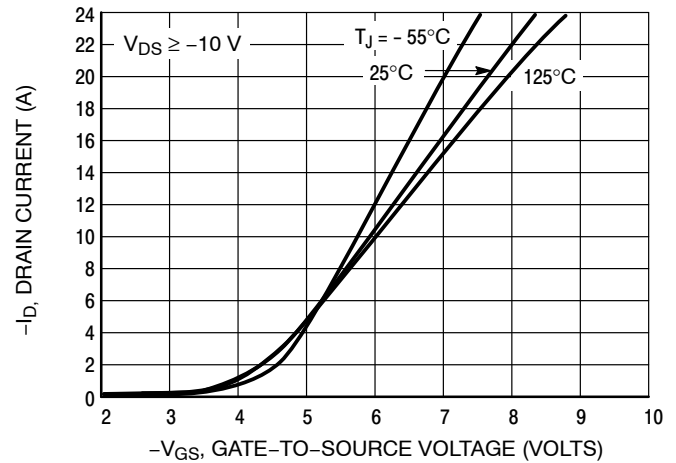


Figure 2. Transfer Characteristics

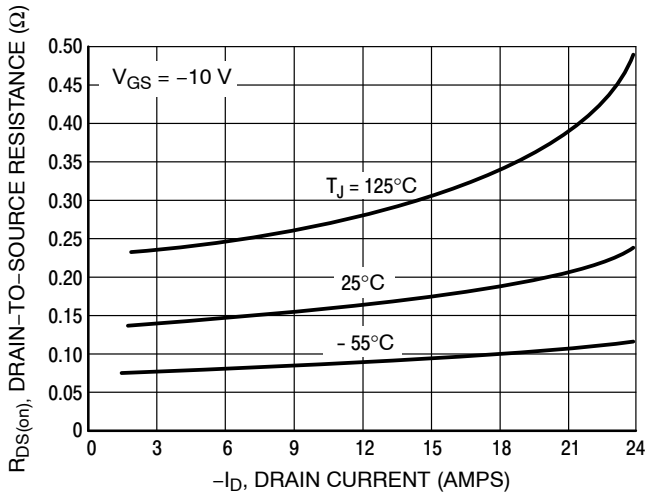


Figure 3. On-Resistance versus Drain Current and Temperature

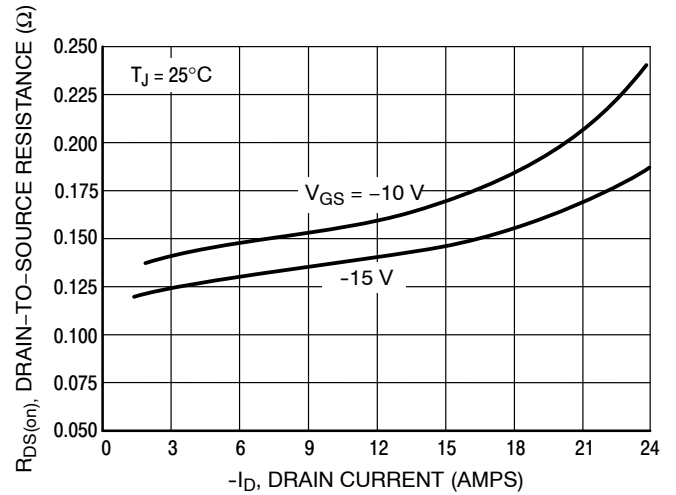


Figure 4. On-Resistance versus Drain Current and Gate Voltage

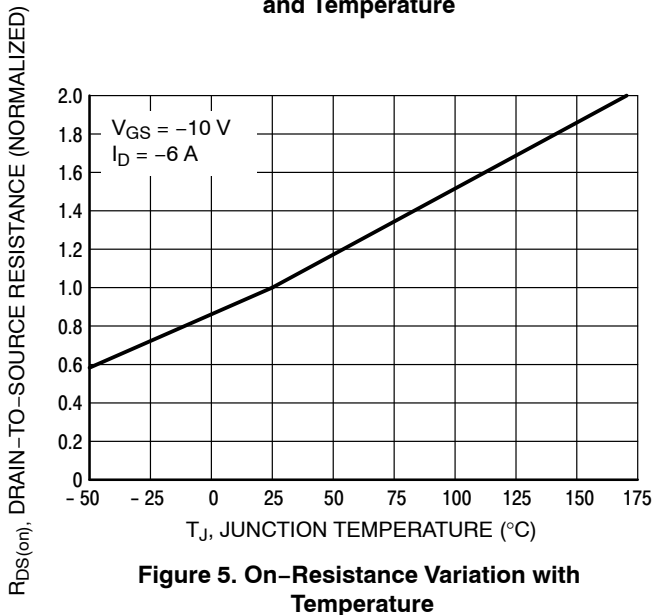


Figure 5. On-Resistance Variation with Temperature

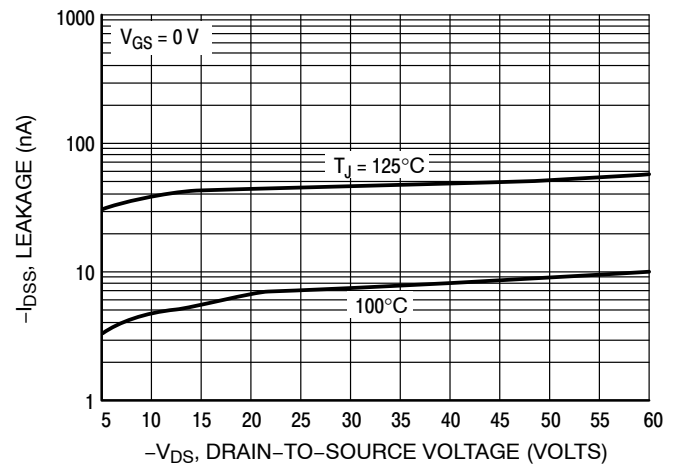


Figure 6. Drain-To-Source Leakage Current versus Voltage

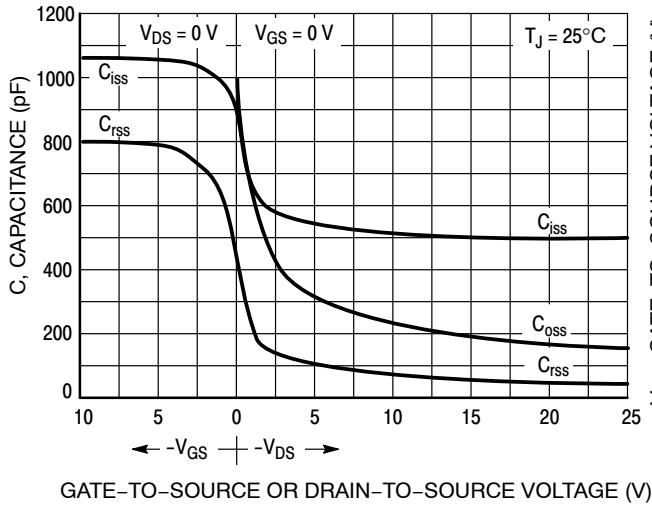


Figure 7. Capacitance Variation

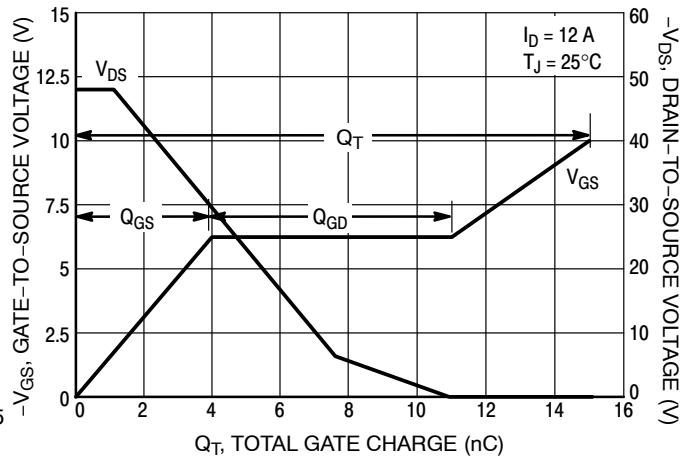


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

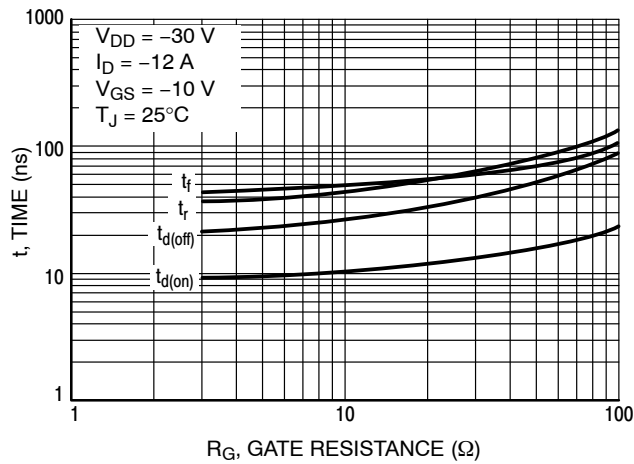


Figure 9. Resistive Switching Time Variation versus Gate Resistance

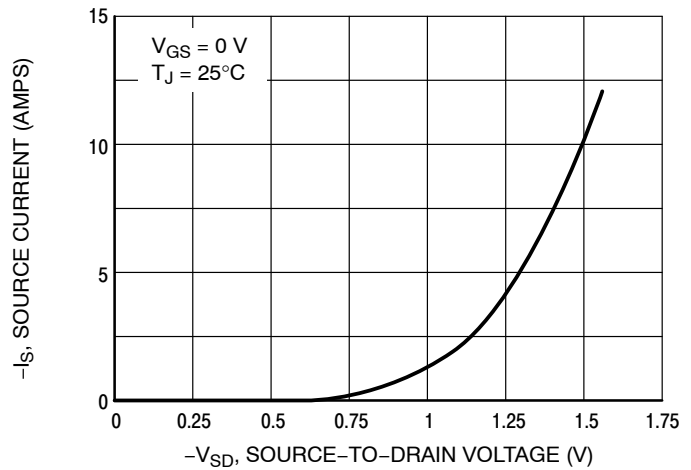


Figure 10. Diode Forward Voltage versus Current

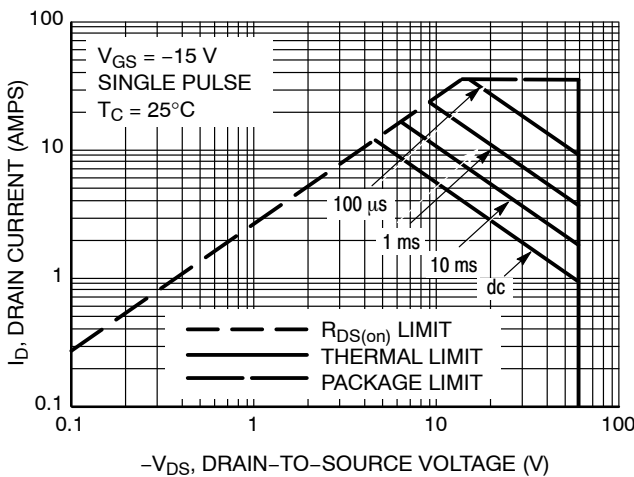


Figure 11. Maximum Rated Forward Biased Safe Operating Area

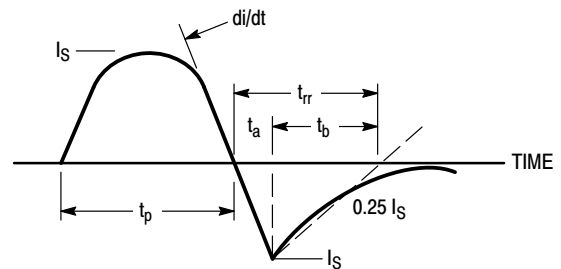


Figure 12. Diode Reverse Recovery Waveform

NTD2955, NVD2955

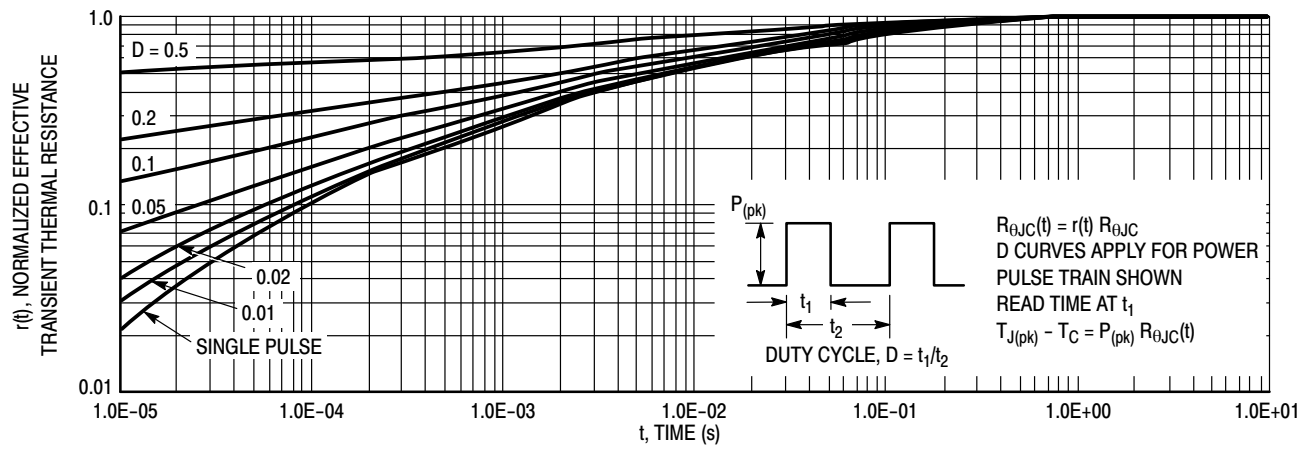


Figure 13. Thermal Response

ORDERING INFORMATION

Device	Package	Shipping [†]
NTD2955G	DPAK (Pb-Free)	75 Units / Rail
NTD2955-1G	IPAK (Pb-Free)	75 Units / Rail
NTD2955T4G	DPAK (Pb-Free)	2500 / Tape & Reel
NVD2955T4G*	DPAK (Pb-Free)	2500 / Tape & Reel
SVD2955T4G*	DPAK (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

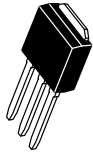
*NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®

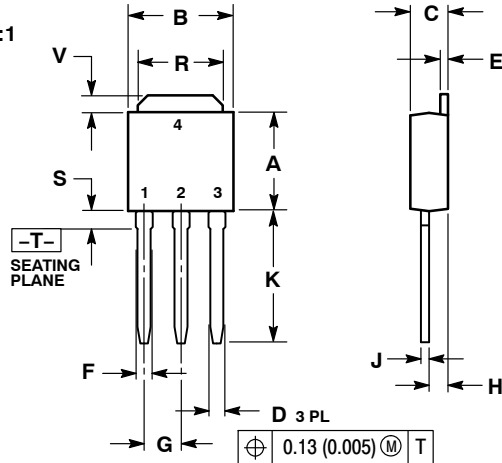
ON



IPAK CASE 369D-01 ISSUE C

DATE 15 DEC 2010

SCALE 1:1



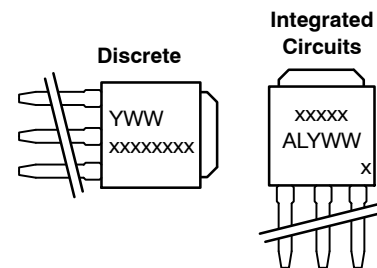
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

MARKING DIAGRAMS

- STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR
- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN
- STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE
- STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE
- STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE
- STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2
- STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

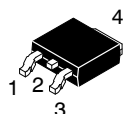


xxxxxxxx = Device Code
A = Assembly Location
IL = Wafer Lot
Y = Year
WW = Work Week

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DESCRIPTION:	IPAK (DPAK INSERTION MOUNT)	PAGE 1 OF 1

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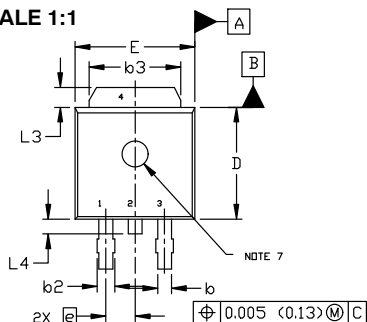
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



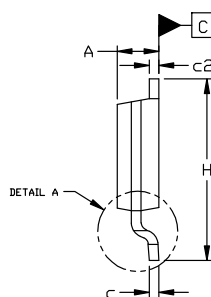
DPAK (SINGLE GAUGE) CASE 369C ISSUE G

DATE 31 MAY 2023

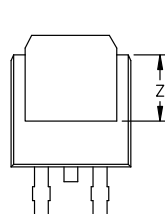
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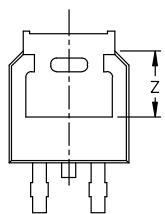
TOP VIEW



SIDE VIEW

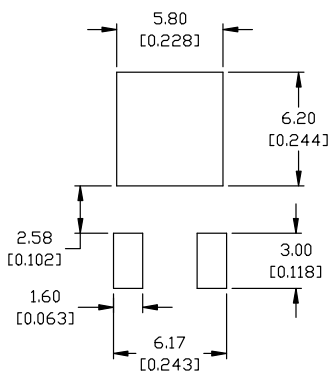


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE
CONSTRUCTIONS



RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:

PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:

PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:

PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:

PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:

PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:

PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:

PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:

PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:

PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

NOTES:

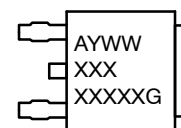
1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---

GENERIC MARKING DIAGRAM*



IC



Discrete

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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